### Innovating Energy Technology

# FMP60N380S2HF

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**FUJI POWER MOSFET** 

## Super J MOS® S2 series

### N-Channel enhancement mode power MOSFET

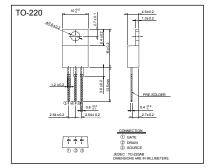
#### Features

Pb-free lead terminal RoHS compliant uses Halogen-free molding compound

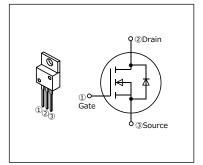
### Applications

For switching

### Outline Drawings [mm]



### Equivalent circuit schematic



### ■ Absolute Maximum Ratings at T<sub>c</sub>=25°C (unless otherwise specified)

Parameter	Symbol	Characteristics	Unit	Remarks
Dunin Course Voltage	<b>V</b> <sub>DS</sub>	600	V	
Drain-Source Voltage	<b>V</b> <sub>DSX</sub>	600	V	V <sub>GS</sub> =-30V
O-mating-range Darwing Organization	,	10	Α	<i>T</i> c=25°C Note*1,2
Continuous Drain Current	<b>/</b> D	6.3	Α	T <sub>c</sub> =100°C Note*1,2
Pulsed Drain Current	<b>I</b> DP	32.4	Α	Note *2
Gate-Source Voltage	<b>V</b> <sub>GS</sub>	±30	V	
Non-Repetitive Maximum Avalanche Current	<b>I</b> AS	1.1	А	Note *3
Non-Repetitive Maximum Avalanche Energy	Eas	380	mJ	Note *4
Maximum Drain-Source dV/dt	d <i>V</i> ⊳s/dt	50	V/ns	V <sub>DS</sub> ≤ 600V
Continuous	1	10	Α	<i>T</i> <sub>c</sub> =25°C Note*1,2
Diode Forward Current	<b>I</b> SD	6.3	Α	<i>T</i> <sub>c</sub> =100°C Note*1,2
Pulsed Diode Forward Current	<b>I</b> SDP	32.4	Α	Note *2
Peak Diode Recovery dV/dt	dV/dt	15	V/ns	Note *5
Peak Diode Recovery -di/dt	-di/dt	100	A/µs	Note *6
Manadana Banasa Birada ada a	P□	2.02	W	<i>T</i> <sub>a</sub> =25°C
Maximum Power Dissipation	FD	62	VV	<i>T</i> <sub>c</sub> =25°C
Operating and Storage Temperature renge	T <sub>ch</sub>	150	°C	
Operating and Storage Temperature range	T <sub>stg</sub>	-55 to +150	°C	

Note \*1 : Maximum duty cycle D=0.65

Note \*1: Maximum duty cycle D=0.50
Note \*2: Limited by maximum channel temperature.

Note \*3: T<sub>ch≤150°</sub>C, See Fig.1 and Fig.2

Note \*4: Starting T<sub>ch=25°C</sub>, I<sub>ss=0.7A</sub>, L=1.42H, V<sub>DD=60V</sub>, R<sub>G=50Ω</sub>, See Fig.1 and Fig.2

E<sub>ss</sub> limited by maximum channel temperature and avalanche current.

Note \*5: I<sub>SD≤8.1A</sub>, -di/dt≤100A/µs, V<sub>DS peak≤600V</sub>, T<sub>ch≤150°C</sub>.

Note \*6: I<sub>SD≤8.1A</sub>, dV/dt≤15V/ns, V<sub>DS peak≤600V</sub>, T<sub>ch≤150°C</sub>.

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# ■ Electrical Characteristics at *T*<sub>c</sub>=25°C (unless otherwise specified) • Static Ratings

Parameter	Symbol	Conditions		min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>cs</sub> =0V I <sub>D</sub> =250μA		600	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =100μA		2.5	3.0	3.5	V
Zero Gate Voltage Drain Current	<b>I</b> DSS	V <sub>DS</sub> =600V V <sub>GS</sub> =0V	T <sub>ch</sub> =25°C	-	-	25	μΑ
		V <sub>DS</sub> =480V V <sub>GS</sub> =0V	T <sub>ch</sub> =125°C	-	-	250	
Gate-Source Leakage Current	<b>I</b> GSS	V <sub>DS</sub> =0V V <sub>GS</sub> = ± 30V		-	10	100	nA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V I <sub>D</sub> =4.1A		-	0.336	0.38	Ω
Gate resistance	<b>R</b> G	f=1MHz, open drain		-	17.2	-	Ω

### Dynamic Ratings

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =25V I <sub>D</sub> =4.1A	3.5	7	-	S
Input Capacitance	Ciss	V <sub>DS</sub> =400V	-	588	-	
Output Capacitance	Coss	V <sub>GS</sub> =0V	-	17.5	-	
Reverse Transfer Capacitance	Crss	f=250kHz	-	3	-	
Effective output capacitance, energy related (Note *7)	C <sub>o(er)</sub>	V <sub>DS</sub> =0400V V <sub>GS</sub> =0V	-	42	-	pF
Effective output capacitance, time related (Note *8)	C <sub>o(tr)</sub>	V <sub>DS</sub> =0400V V <sub>GS</sub> =0V I <sub>D</sub> =constant	-	138	-	
Turn-On Time	t <sub>d(on)</sub>	$V_{\text{DD}}$ =400V, $V_{\text{GS}}$ =10V $I_{\text{D}}$ =4.1A, $R_{\text{G}}$ =18 $\Omega$ See Fig.3 and Fig.4	-	12.5	-	
Turn-On Time	<b>t</b> r		-	22.5	-	20
Turn-Off Time	t <sub>d(off)</sub>		-	89.5	-	ns
Turni-On Time	<b>t</b> f		-	21	-	
Total Gate Charge	<b>Q</b> <sub>G</sub>	V <sub>DD</sub> =400V, V <sub>GS</sub> =10V I <sub>D</sub> =8.1A See Fig.5	-	27.5	-	
Gate-Source Charge	<b>Q</b> GS		-	8	-	nC
Gate-Drain Charge	<b>Q</b> <sub>GD</sub>		-	7.5	-	nC
Drain-Source crossover Charge	<b>Q</b> sw		-	5	-	

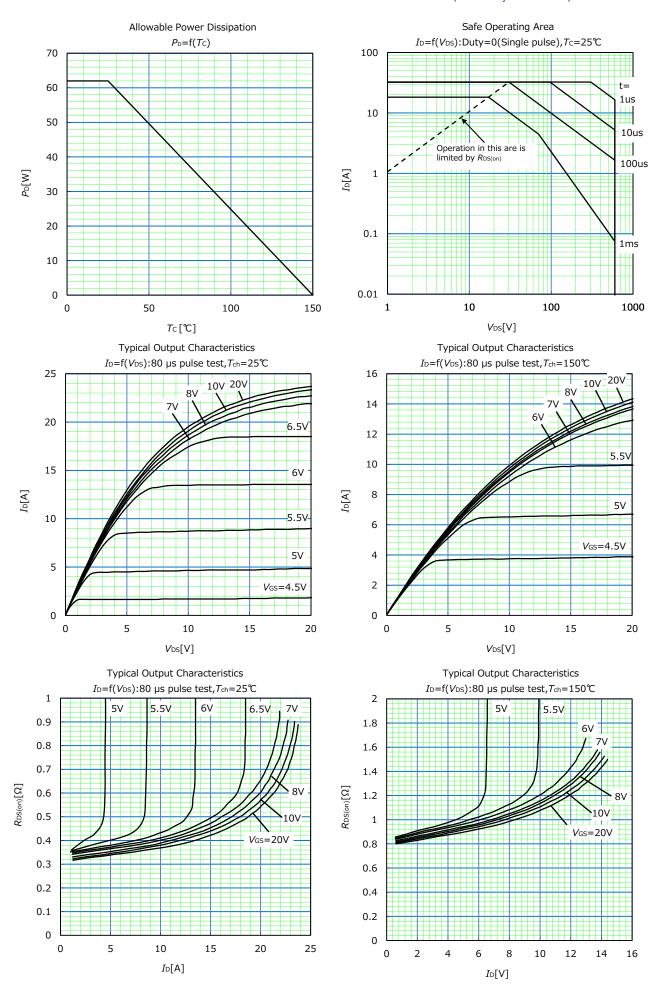
Note  $^*7$ :  $C_{0(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{Ds}$  is rising from 0 to 400V. Note  $^*8$ :  $C_{o(er)}$  is a fixed capacitance that gives the same charging times as  $C_{oss}$  while  $V_{Ds}$  is rising from 0 to 400V.

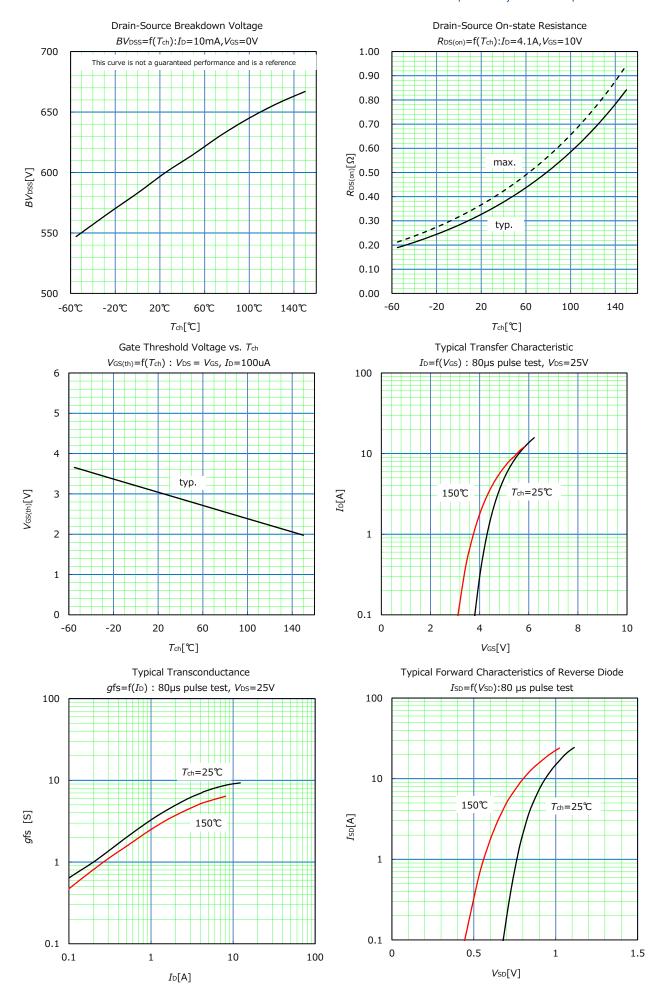
### Reverse Diode

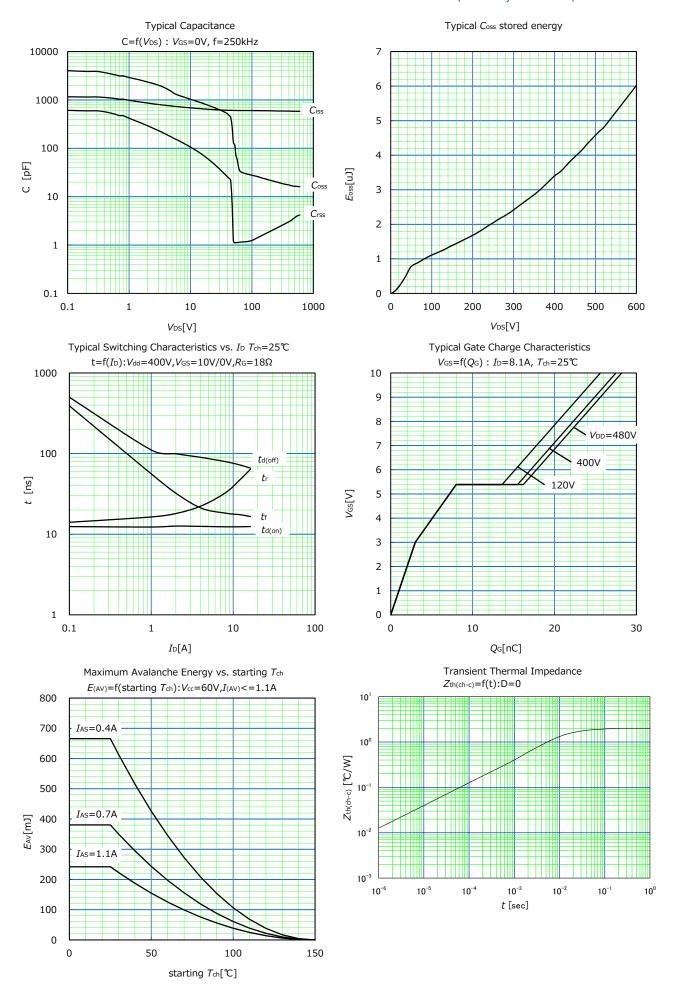
Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Diode Forward On-Voltage	<b>V</b> <sub>SD</sub>	I <sub>SD</sub> =8.1A, V <sub>GS</sub> =0V T <sub>ch</sub> =25°C	-	0.9	1.35	V
Reverse Recovery Time	<b>t</b> rr	$V_{\text{DD}}$ =400V, $I_{\text{SD}}$ =8.1A -di/dt=100A/ $\mu$ s $T_{\text{ch}}$ =25°C See Fig.6 and Fig.7	-	270	-	ns
Reverse Recovery Charge	Qrr		-	2.6	-	μC
Peak Reverse Recovery Current	<b>I</b> rp		-	18.7	-	Α

### ■ Thermal Resistance

Parameter	Symbol	min.	typ.	max.	Unit
Channel to Case	R <sub>th(ch-c)</sub>	-	-	2.016	°C/W
Channel to Ambient	R <sub>th(ch-a)</sub>	-	-	62	°C/W







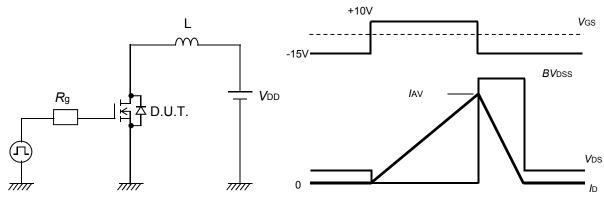


Fig.1 Avalanche Test circuit

Fig.2 Operating waveforms of Avalanche Test

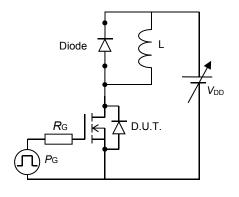


Fig.3 Switching Test circuit

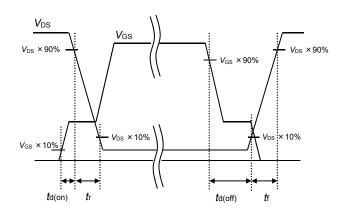


Fig.4 Operating waveform of Switching Test

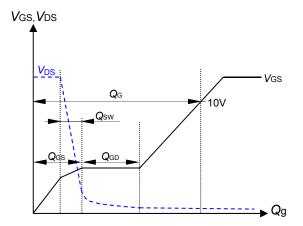


Fig.5 Operating waveform of Gate charge Test

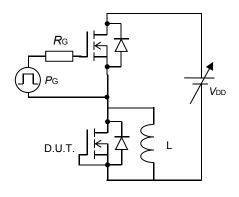


Fig.6 Reverse recovery Test circuit

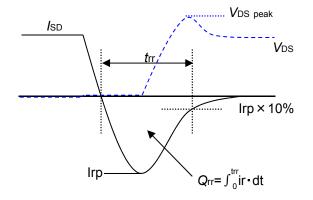
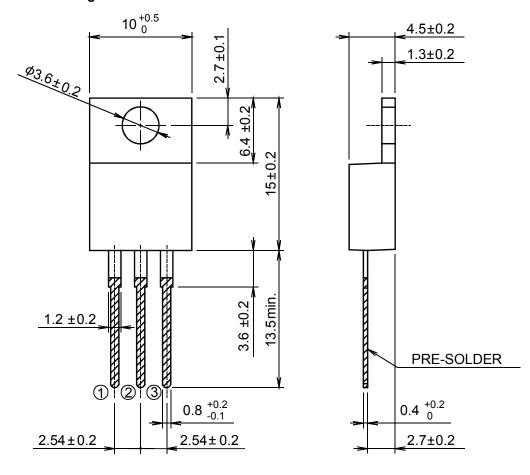
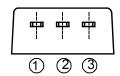


Fig.7 Operating waveform of Reverse recovery Test

### Outview: TO-220 Package





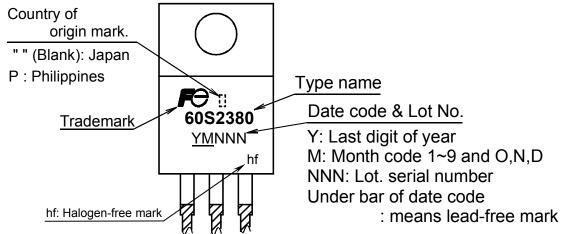
### CONNECTION

- 1 GATE
- 2 DRAIN
- 3 SOURCE

JEDEC: TO-220AB

DIMENSIONS ARE IN MILLIMETERS.

### Marking



\* The font (font type,size) and the trademark-size might be actually different.

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